FDG332PZ-VB Datasheet

P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)[a]	Q_g (Typ.)
- 20	0.034 at V_{GS} = - 4.5 V	- 4	12.5 nC
	0.045 at V_{GS} = - 2.5 V	- 4	
	0.067 at V_{GS} = - 1.8 V	- 4	

FEATURES

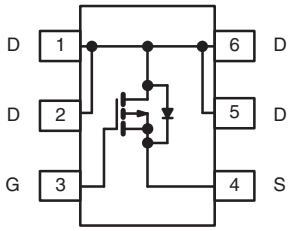
- **Halogen-free According to IEC 61249-2-21 Definition**
- Trench Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

Pb-free
RoHS COMPLIANT

APPLICATIONS

- Load Switch for Portable Devices
  - Cellular Phone
  - DSC
  - Portable Game Console
  - MP3
  - GPS

SOT-363
SC-70 (6-LEADS)



Top View

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	- 20	V
Gate-Source Voltage		V_{GS}	± 12	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	- 4[a]	A
	T_C = 70 °C		- 4	
	T_A = 25 °C		- 4[a, b, c]	
	T_A = 70 °C		- 4[a, b, c]	
Pulsed Drain Current (t = 300 µs)		I_{DM}	- 25	
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	- 2.3	
	T_A = 25 °C		- 1.3[b, c]	
Maximum Power Dissipation	T_C = 25 °C	P_D	2.8	W
	T_C = 70 °C		1.8	
	T_A = 25 °C		1.6[b, c]	
	T_A = 70 °C		1.0[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature)			260	

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient[b, d]	t ≤ 5 s	R_{thJA}	60	80	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	34	45	

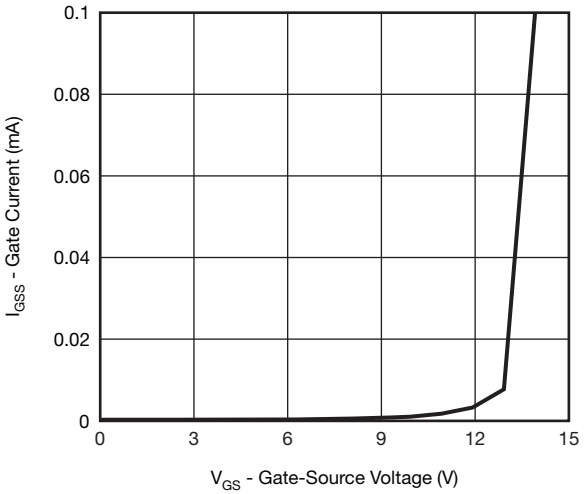
Notes:
a. Package limited.
b. Surface mounted on 1" x 1" FR4 board.
c. t = 5 s.
d. Maximum under steady state conditions is 125 °C/W.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = - 250 µA	- 20			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = - 250 µA		- 11		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			2.6		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA	- 0.4		- 1	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 10 V			± 8	µA
		V_{DS} = 0 V, V_{GS} = ± 4.5 V			± 1	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 20 V, V_{GS} = 0 V			- 1	
		V_{DS} = - 20 V, V_{GS} = 0 V, T_J = 55 °C			- 10	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \leq$ - 5 V, V_{GS} = - 10 V	- 15			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 4.5 V, I_D = - 5 A		0.034		Ω
		V_{GS} = - 2.5 V, I_D = - 4.4 A		0.045		
		V_{GS} = - 1.8 V, I_D = - 1 A		0.067		
Forward Transconductance[a]	g_{fs}	V_{DS} = - 10 V, I_D = - 5 A		16		S
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = - 10 V, V_{GS} = - 8 V, I_D = - 5 A		22	33	nC
Gate-Source Charge		V_{DS} = - 10 V, V_{GS} = - 4.5 V, I_D = - 5 A		12.5	19	
	Q_{gs}			1.8		
Gate-Drain Charge	Q_{gd}			3.3		
Gate Resistance	R_g	f = 1 MHz	0.08	0.43	0.86	kΩ
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 10 V, R_L = 1.4 Ω $I_D \cong$ - 4 A, V_{GEN} = - 4.5 V, R_g = 1 Ω		150	225	ns
Rise Time	t_r			300	450	
Turn-Off Delay Time	$t_{d(off)}$			1620	2430	
Fall Time	t_f			560	840	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 10 V, R_L = 1.4 Ω $I_D \cong$ - 4 A, V_{GEN} = - 10 V, R_g = 1 Ω		50	100	
Rise Time	t_r			90	180	
Turn-Off Delay Time	$t_{d(off)}$			2500	3750	
Fall Time	t_f			600	900	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C			- 2.3	A
Pulse Diode Forward Current	I_{SM}				- 25	
Body Diode Voltage	V_{SD}	I_S = - 4 A, V_{GS} = 0 V		- 0.85	- 1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = - 4 A, dI/dt = 100 A/µs, T_J = 25 °C		18	36	ns
Body Diode Reverse Recovery Charge	Q_{rr}			8	16	nC
Reverse Recovery Fall Time	t_a			18		ns
Reverse Recovery Rise Time	t_b			10		

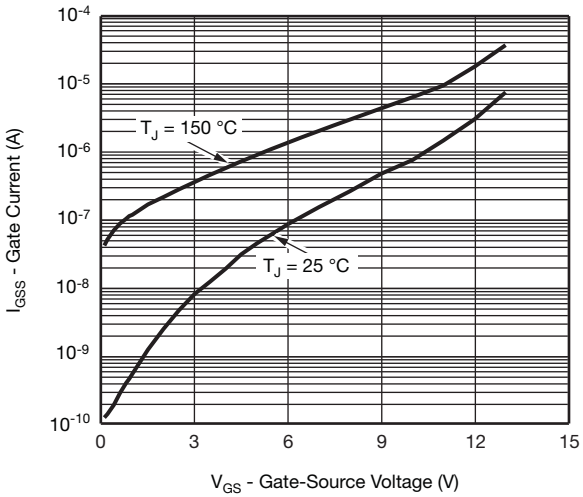
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

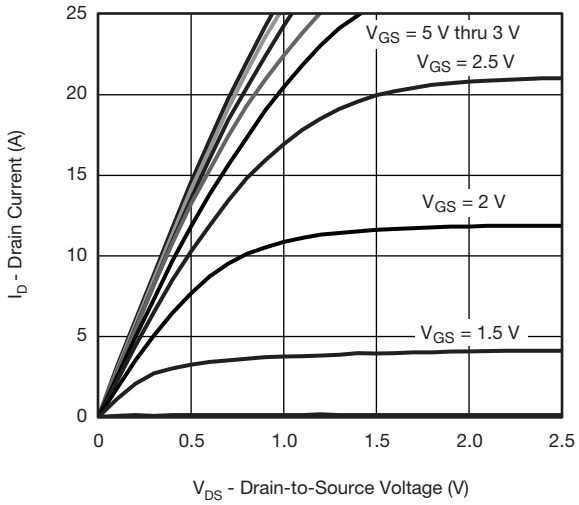
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



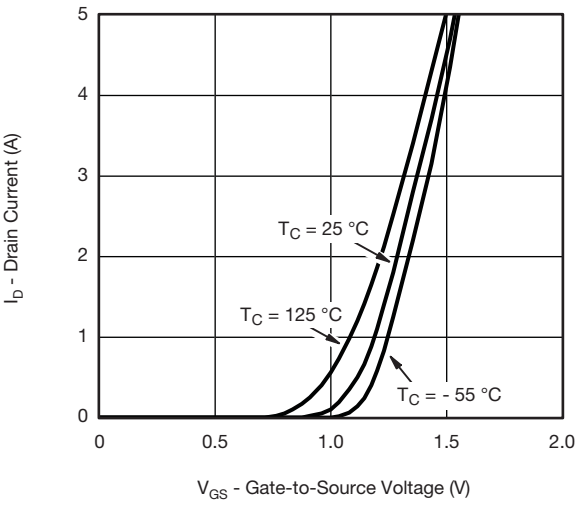
Gate Current vs. Gate-Source Voltage



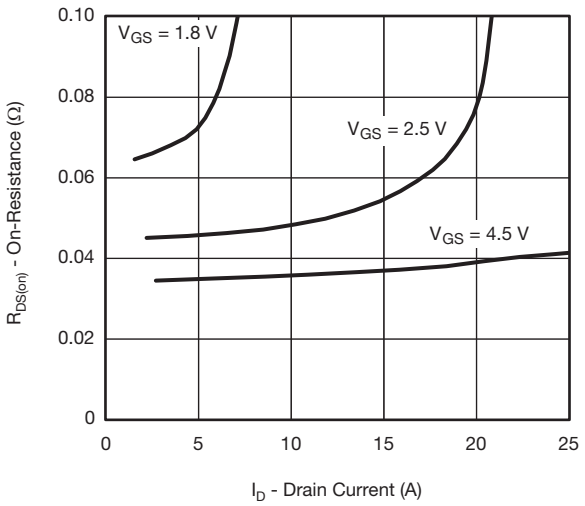
Gate Current vs. Gate-Source Voltage



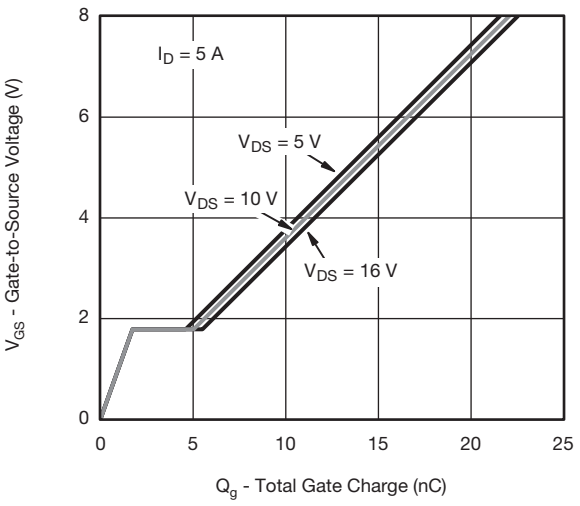
Output Characteristics



Transfer Characteristics

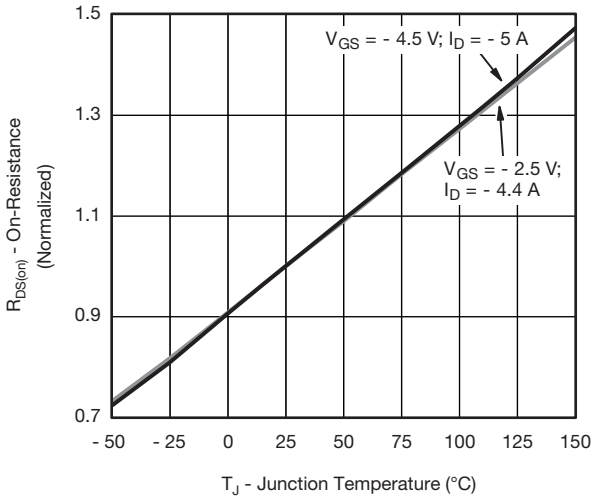


On-Resistance vs. Drain Current

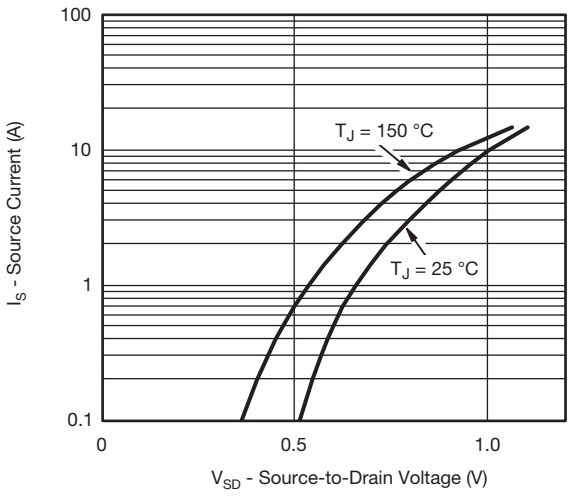


Gate Charge

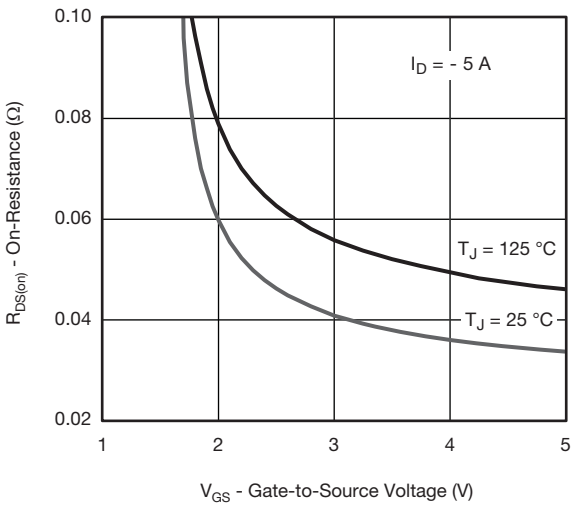
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



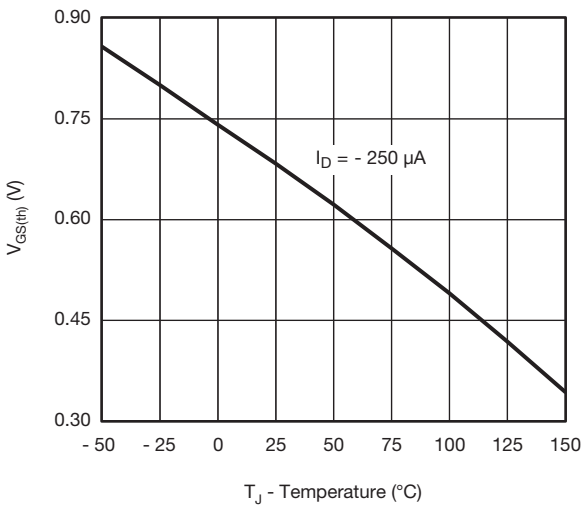
On-Resistance vs. Junction Temperature



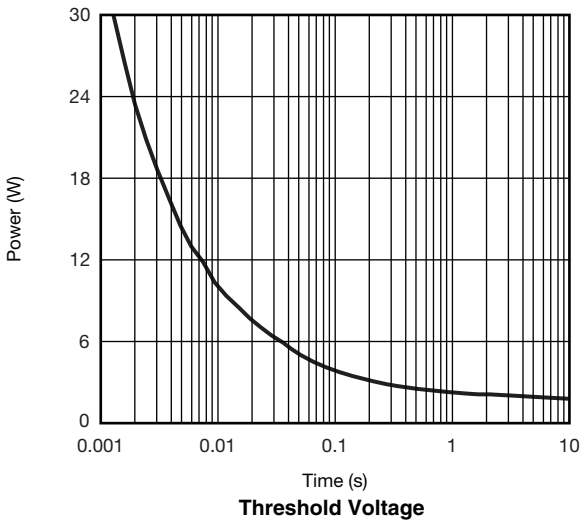
Source-Drain Diode Forward Voltage



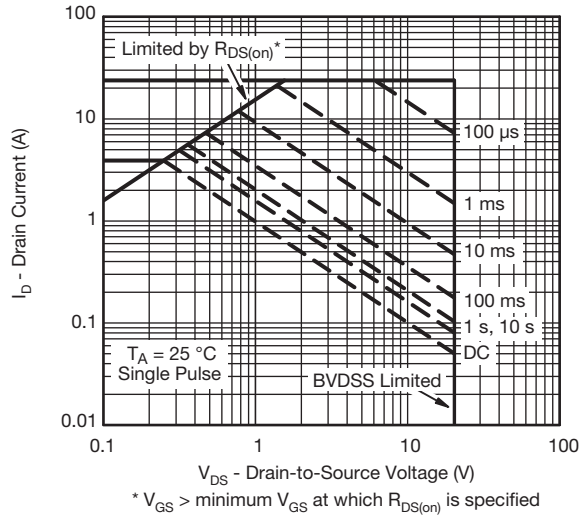
On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient



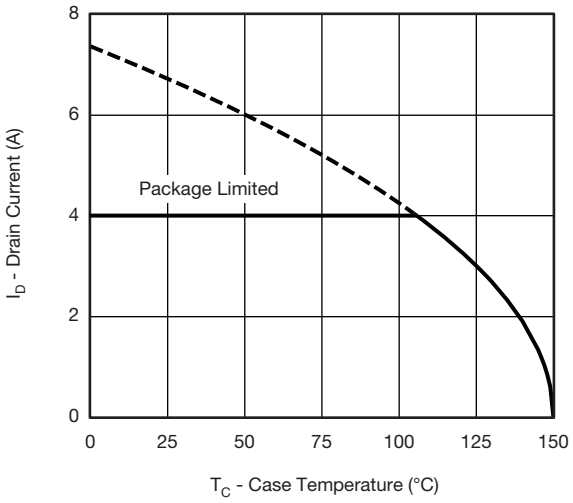
Threshold Voltage



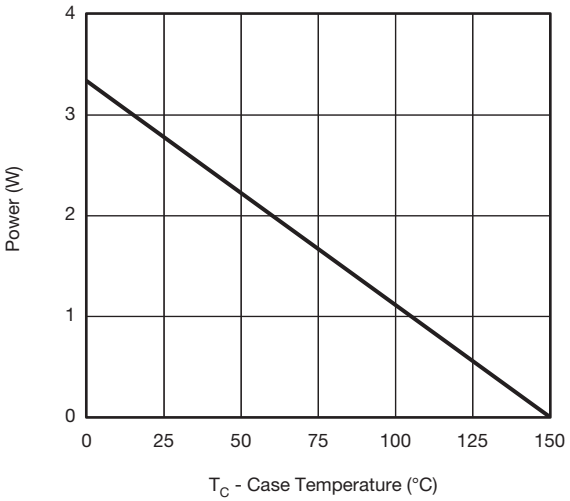
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

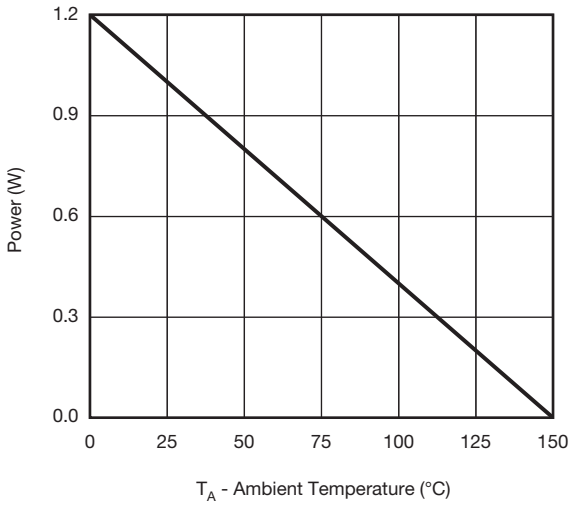
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



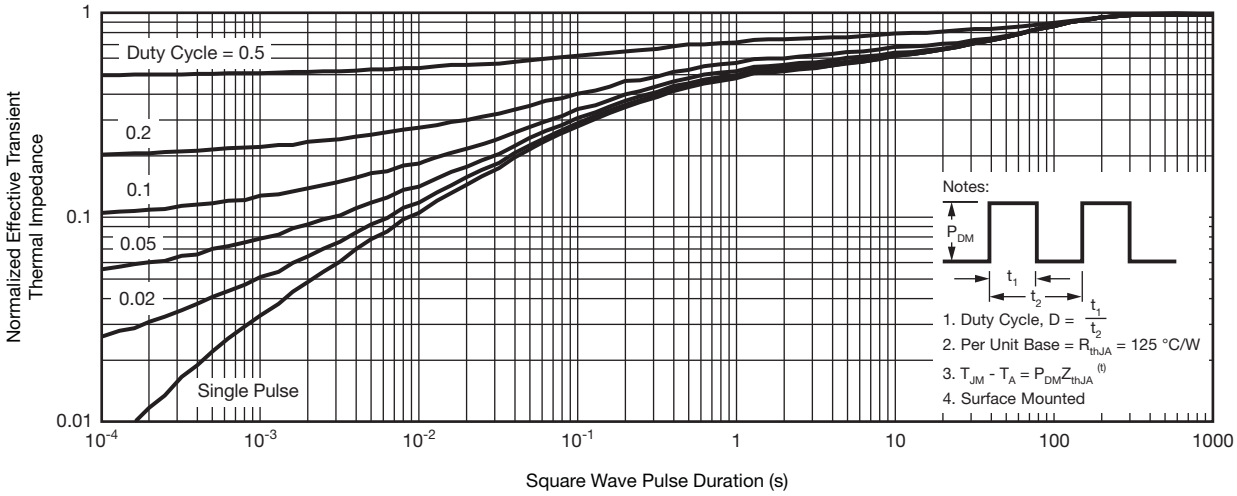
Power Derating, Junction-to-Foot



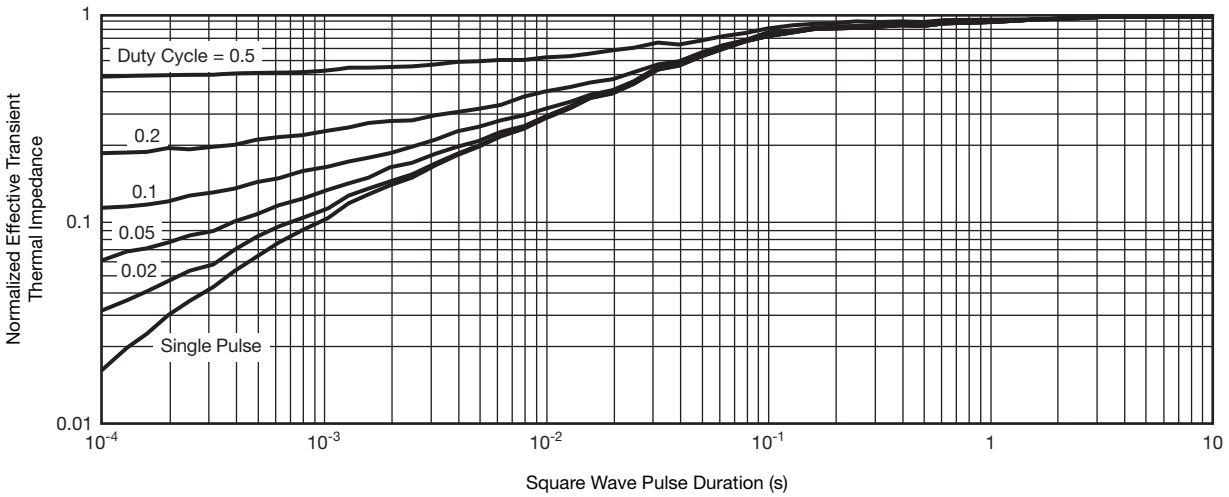
Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

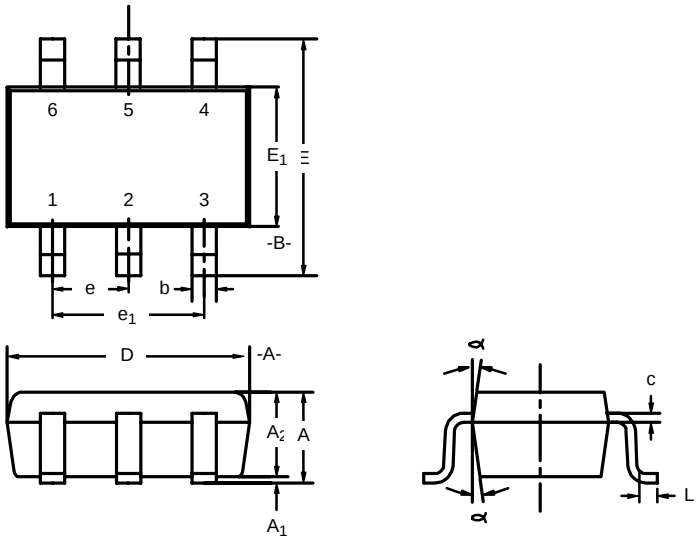


Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

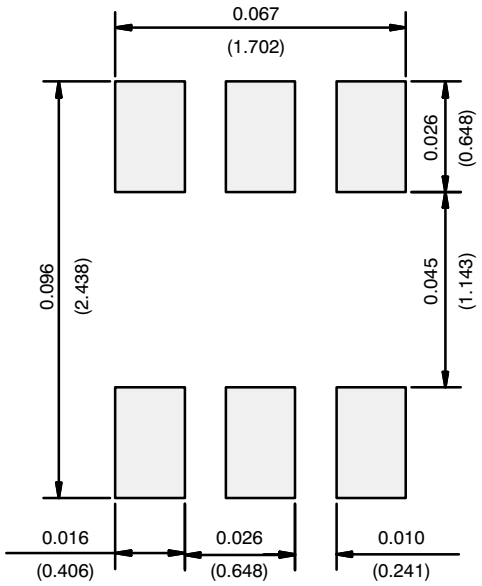
SC-70: 6-LEADS



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.90	–	1.10	0.035	–	0.043
A_1	–	–	0.10	–	–	0.004
A_2	0.80	–	1.00	0.031	–	0.039
b	0.15	–	0.30	0.006	–	0.012
c	0.10	–	0.25	0.004	–	0.010
D	1.80	2.00	2.20	0.071	0.079	0.087
E	1.80	2.10	2.40	0.071	0.083	0.094
E_1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65BSC			0.026BSC		
e_1	1.20	1.30	1.40	0.047	0.051	0.055
L	0.10	0.20	0.30	0.004	0.008	0.012
α	7°Nom			7°Nom		

ECN: S-03946—Rev. B, 09-Jul-01
DWG: 5550

RECOMMENDED MINIMUM PADS FOR SC-70: 6-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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